

# isc N-Channel MOSFET Transistor

2SK3979-D

#### **FEATURES**

- Drain Current : I<sub>D</sub>= 4A@ T<sub>C</sub>=25℃
- Drain Source Voltage
  - : V<sub>DSS</sub>= 200V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 550 \text{m} \Omega \text{ (Max)} @V_{GS} = 10 \text{V}$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **DESCRIPTION**

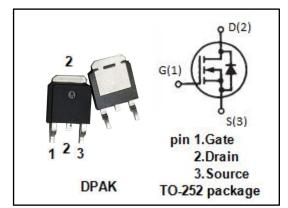
 motor drive, DC-DC converter, power switch and solenoid drive.

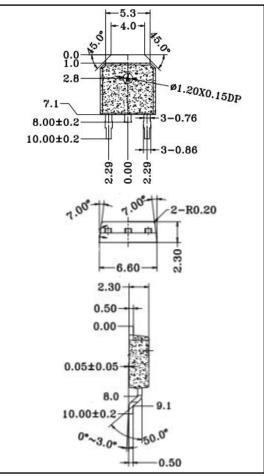
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                                   | VALUE | UNIT          |
|------------------|---|-------|---------------|
| V <sub>DSS</sub> | Drain-Source Voltage                        | 200   | V             |
| V <sub>GS</sub>  | Gate-Source Voltage-Continuous              | ±20   | V             |
| I <sub>D</sub>   | Drain Current-Continuous                    | 6.0   | А             |
| I <sub>DM</sub>  | Drain Current-Single Pluse                  | 24    | А             |
| P <sub>D</sub>   | Total Dissipation @Tc=25℃ 20                |       | W             |
| TJ               | Max. Operating Junction Temperature -55~150 |       | $^{\circ}$    |
| T <sub>stg</sub> | Storage Temperature -55~150                 |       | ${\mathbb C}$ |

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | MAX  | UNIT |
|---------------------|--------------------------------------|------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 6.25 | °C/W |







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS                                  | MIN | MAX | UNIT |
|----------------------|---------------------------------|---|-----|-----|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA   | 200 |     | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = 10V; I <sub>D</sub> = 1mA | 2.0 | 3.2 | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 3A  |     | 450 | m Ω  |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0  |     | ±10 | uA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 200V; V <sub>GS</sub> = 0 |     | 1.0 | uA   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = 6A; V <sub>GS</sub> = 0    |     | 1.2 | V    |

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